

In the Specification

C1 [0015] The structure of FIG. 1 is subjected to an inventive etch as described above. An exemplary etch includes processing the wafer in a chamber of an AME5000 etch chamber. After placing the wafer substrate assembly in the etch chamber, O_2 and CHF_3 or CH_2F_2 are introduced into the chamber at flow rates of about 60 sccm and about 20 sccm respectively. Pressure is maintained at between about 30 millitorr and about 40 millitorr, and a power of between about 300 watts and about 400 watts is utilized. At a chuck temperature of about $10^\circ C$ and a sidewall temperature of about $20^\circ C$, the silicon nitride will etch at a rate of about $720 \text{ \AA}/\text{min}$ in the vertical direction, and about $180 \text{ \AA}/\text{min}$ in the horizontal direction. Generally, the vertical:horizontal etch rate will be about 4:1. For the 525 \AA thick layer of silicon nitride depicted in FIG. 1, the etch is performed ~~in the absence of a photoresist layer~~ for between about 35 seconds and about 60 seconds which results in the structure of FIG. 2. Spacers 32 having a width of about 300 \AA to about 400 \AA are formed.